

SECTION I (AMENDMENTS TO THE CLAIMS)

A listing of claims 1-20 of the present application, which are amended herein with markings to show changes made, is provided below:

1. (Currently amended) An interconnect structure comprising:
 - a semiconductor substrate comprising one or more device regions; and
 - one or more interconnect levels located atop the semiconductor substrate, said one or more interconnect levels comprising a patterned organosilicate dielectric having sidewalls, wherein said sidewalls ~~are not substantially altered either chemically or physically~~ comprise CH₃ species with x = 1-3.
2. (Original) The interconnect structure of Claim 1 wherein said patterned organosilicate dielectric has a dielectric constant of less than 4.0.
3. (Original) The interconnect structure of Claim 1 wherein said one or more interconnect levels include metal lines and vias.
4. (Original) The interconnect structure of Claim 3 wherein the metal lines and vias comprise a conductive material.
5. (Original) The interconnect structure of Claim 1 wherein said one or more interconnect levels form a tinwire interconnect structure.
6. (Previously presented) The interconnect structure of Claim 1 wherein said one or more interconnect levels form a fatwire interconnect structure.

7. (Original) The interconnect structure of Claim 1 wherein said one or more device regions comprise a field effect transistor.

8-20. (Cancelled).